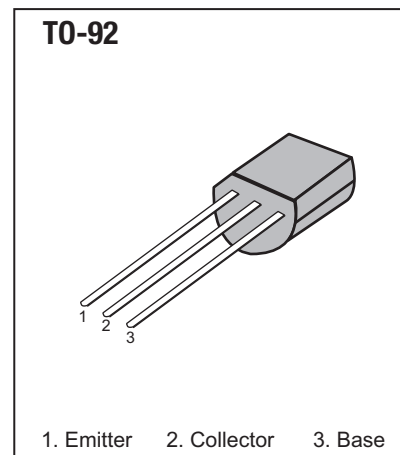
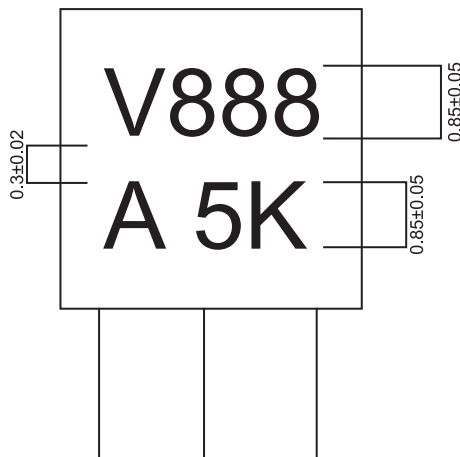


### 1. Ultra Low-Noise Audio Amplifier Applications

The 2SV888 is a PNP epitaxial transistor which has been optimized for use in audio applications. The ultra-low input voltage noise of the 2SV888 is typically only 0.3 dB over the entire audio bandwidth of 20 Hz to 20 kHz. Its ultra-low noise, high bandwidth and high current gain make the 2SV888 an ideal choice for demanding ultra-low noise preamplifier applications.

### 2. Ultra Low-Noise Audio Amplifier Applications

- **Low-noise: NF=2dB(typ.)  $R_G=100\Omega$ ,  $V_{CE}=6V$ ,  $I_c=100\mu A$ ,  $f=1kHz$   
: NF=0.3dB(typ.)  $R_G=1k\Omega$ ,  $V_{CE}=6V$ ,  $I_c=100\mu A$ ,  $f=1kHz$**
- **High DC current gain:  $H_{FE}=200-700$**
- **High breakdown voltage:  $V_{CEO}=-120V$**
- **Low pulse noise. Low 1/f noise**



Information furnished by COOLAUDIO is believed to be accurate and reliable. However, no responsibility is assumed by COOLAUDIO for its use, nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of COOLAUDIO.

Rev. 1.0

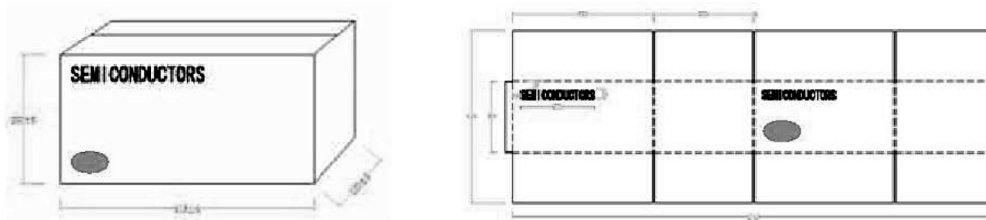
### 3. Absolute Maximum Ratings (T<sub>a</sub>=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-120	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-120	V
Emitter-Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current (DC)	I <sub>C</sub>	-100	mA
Base Current (DC)	I <sub>B</sub>	-20	mA
Collector Dissipation	P <sub>C</sub>	300	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55-150	°C

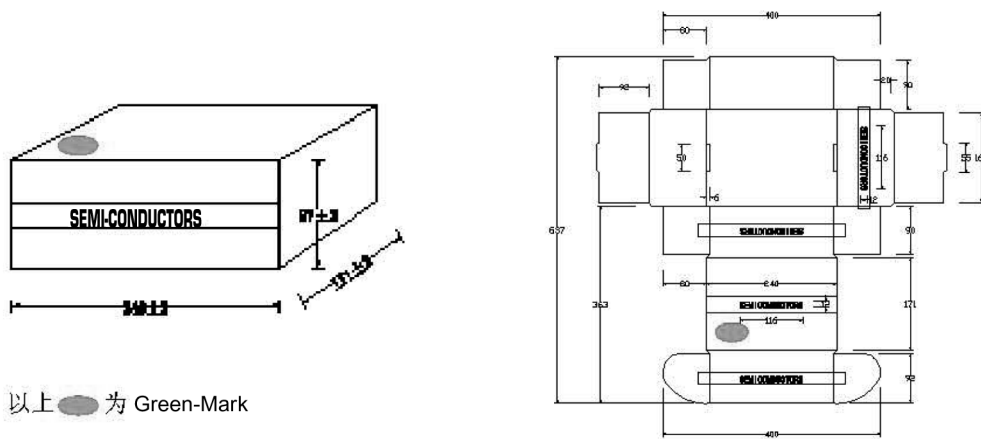
### 4. Electrical Characteristics (T<sub>a</sub>=25°C)


Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =-120V, I <sub>E</sub> =0			-0.1	µA
Emitter Cut-off Current	I <sub>EB0</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	µA
Collector-Emitter Breakdown Voltage	BV <sub>CE0</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-120			V
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	I <sub>E</sub> =-100µA, I <sub>C</sub> =0	-5			V
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	I <sub>C</sub> =-100µA, I <sub>E</sub> =0	-120			V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-0.3	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-2mA		-0.65		V
DC Current Gain	H <sub>FE1</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-2mA	200		700	
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-1mA		100		MHz
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		4.0		pF
Noise Figure	NF	V <sub>CE</sub> =-6V, I <sub>C</sub> =-0.1mA, f=10Hz, R <sub>G</sub> =10k Ω			4	dB
		V <sub>CE</sub> =-6V, I <sub>C</sub> =-0.1mA, f=1kHz, R <sub>G</sub> =10k Ω			1.2	
		V <sub>CE</sub> =-6V, I <sub>C</sub> =-0.1mA, f=1kHz, R <sub>G</sub> =100 Ω		2		

**a. Box1**



**b. Box2**



以上  为 Green-Mark

	Plastic Bag	Box		
		Bags/Box2	Box2/Box1	Pcs/Box1
Packing	Pcs/Bag			
2SA970GR	1000	10	10	100,000

**c. Green-Mark**



Name of the Part	Material Weight (mg/unit)	Material Name	Material Analysis (element)	Material Analysis (weight%)
Leadframe	27	PMC	Fe Zn P Cu	2.4% 0.03% 0.12% 97.45%
Plastic	47	Epoxy Resin	Epoxy Resin SiO <sub>2</sub> 酚醛 脱膜剂 其它微量元素	15% 73% 8% <1% 约3%
Chip	1.25	Doped Silicon	Si Al	99.4% 0.6%
Wires	5	Gold	Au	99.99
Leads Finishing	0.25	Lead-Free	Pb<100ppm	